High-voltage Switching Transistor (Telephone, Power supply) (-600V, -1A) 2SA1807

Features

- 1) High breakdown voltage. (BV_{CEO}=-600V)
- 2) Low saturation voltage, typically VcE(sat) =–0.25V at Ic / IB=–300mA / –60mA.
- 3 $\rangle\,$ High switching speed, typically tf=0.4 $\mu\,s$ at Ic=-500mA
- 4) Wide SOA (safe operating area).

Packaging specifications and hre

Туре	2SA1807
Package	CPT3
hfe	NP
Code	TL
Basic ordering unit (pieces)	2500

Symbol	Limits	Unit
Vсво	-600	V
VCEO	-600	V
Vebo	-7	V
lc	-1	A (DC)
	-2	A (Pulse) *
D.	1	W
FC	10	W(Tc=25°C)
Tj	150	°C
Tstg	-55~+150	Ĵ
	VCBO VCEO VEBO IC PC Tj	VCBO -600 VCEO -600 VEBO -7 Ic -1 Pc 1 Tj 150

* Single pulse, Pw=100ms

●Absolute maximum ratings (Ta=25℃)

●Electrical characteristics (Ta=25℃)

Parameter	Symbol	Min,	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-600	_	—	V	Ic=-50 μ A
Collector-emitter breakdown voltage	BVCEO	-600	_		V	Ic=-1mA
Emitter-base breakdown voltage	BVево	-7	_	_	V	$I_E = -50 \ \mu A$
Collector cutoff current	Ісво	—	-	-10	μA	V _{CB} =-600V
Emitter cutoff current	Іево	—	_	-10	μA	VEB=-7V
Collector-emitter saturation voltage	VCE(sat)	—	-0.25	-1	V	Ic/IB=-300mA/-60mA
Base-emitter saturation voltage	VCE(sat)	—	-	-1.2	V	Ic/IB=-300mA/-60mA
DC current transfer ratio	hfe	56	_	180	—	VCE=-5V, IC=-100mA
Transition frequency	f⊤	—	15	_	MHz	Vсв=-10V, IE=50mA, f=5MHz
Output capacitance	Cob	—	40	—	pF	VCE=-10V, IE=0A, f=1MHz
Turn-on time	ton	_	0.2	-	μs	Ic=-500mA, RL=500Ω
Storage time	t stg	—	1.8	—	μs	$I_{B1} = -I_{B2} = -100 \text{mA}$
Fall time	tr	—	0.4	-	μs	Vcc <u>~</u> -250V

(96-102-A331)

High-voltage Switching Transistor (Telephone, Power supply) (-400V, -2A) 2SA1862

Features

- 1) High breakdown voltage. (BVcEo=-400V)
- 2) Low saturation voltage, typically V_{CE(sat)} =-0.3V at lc / I_B=-500mA / -100mA.
- 3) High switching speed, typically tf=0.4 μ s at Ic=-1A.
- 4) Wide SOA (safe operating area).

Packaging specifications and hre

Туре	2SA1862
Package	CPT3
hfe	Р
Code	TL
Basic ordering unit (pieces)	2500

●Absolute maximum ratings(Ta=25℃)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	-400	V	
Collector-emitter voltage	VCEO	-400	V	
Emitter-base voltage	Vebo	-7	V	
Collector current	lc	-2	A (DC)	
		-4	A (Pulse) 🛛 🛪	
Collector power dissipation	D-	1	W	
	Po	10	W(Tc=25°C)	
Junction temperature	Tj	150	C	
Storage temperature	Tstg	-55~+150	Ĵ	

* Single pulse, Pw=10ms

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-400	-	-	V	$I_{C} = -50 \mu A$
Collector-emitter breakdown voltage	BVCEO	-400	-	—	V	Ic=-1mA
Emitter-base breakdown voltage	BV EBO	-7	-	—	V	$I_E = -50 \mu A$
Collector cutoff current	Ісво	—	—	-10	μA	V _{CB} =-400V
Emitter cutoff current	Іево	_	-	-10	μA	VEB=-5V
Collector-emitter saturation voltage	VCE(sat)	—	-0.3	-0.5	V	Ic/IB=-0.5A/-0.1A
Base-emitter saturation voltage	VCE(sat)	—	—	-1.2	V	Ic/IB=-0.5A/-0.1A
DC current transfer ratio	ĥfe	82	—	180	_	Vce=-5V, Ic=-0.1A
Transition frequency	f⊤	_	18	-	MHz	VCB=-10V , IE=0.1A , f=5MHz
Output capacitance	Cob	_	30	_	pF	Vce=-10V, le=0A, f=1MHz
Turn-on time	ton	—	0.2	_	μs	Ic=-1A, RL=150Ω
Storage time	tsig	—	1.8	—	μs	IB1=-IB2=-0.2A
Fall time	tr	—	0.4	—	μs	Vcc <u>∼</u> 150V

(96-109-A343)



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